

N-Channel Depletion-Mode MOSFET

DESIGNED FOR:

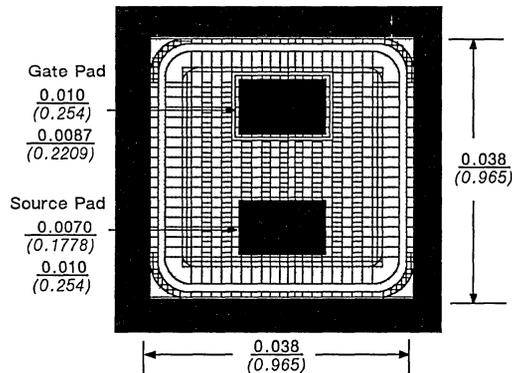
- Switching
- Amplification

FEATURES

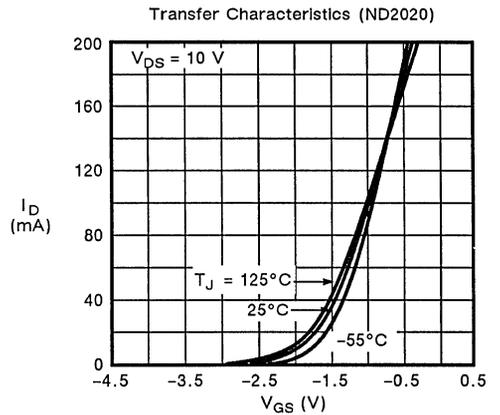
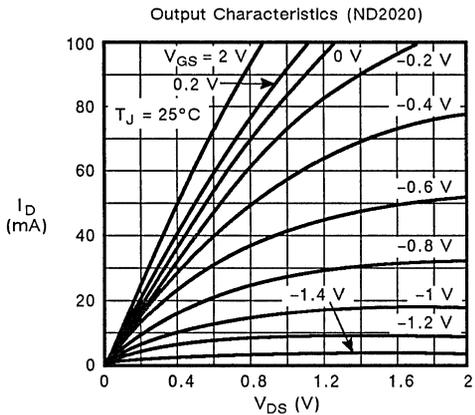
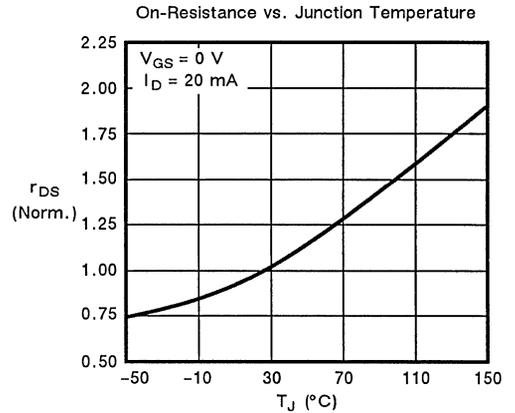
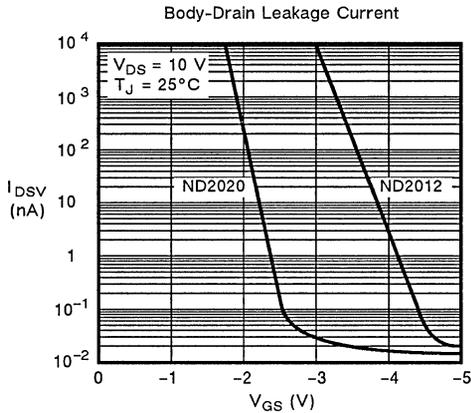
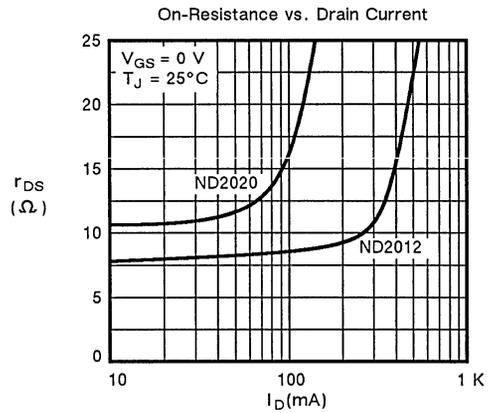
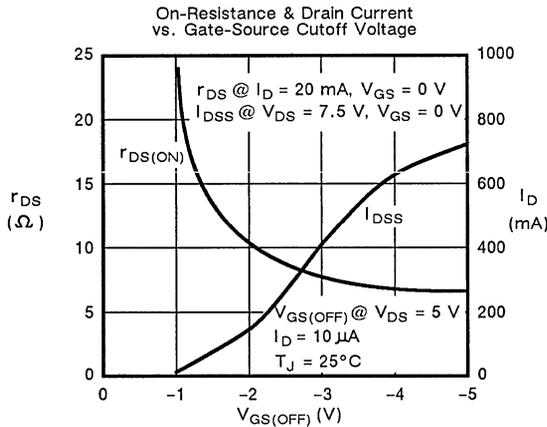
- High Breakdown Voltage > 200 V
- Low $r_{DS(on)} < 3 \Omega$

TYPE	PACKAGE	DEVICE
Single	TO-206AC	• ND2012E, ND2020E
	TO-92	• ND2012L, ND2020L
	Chip	• Available as above specifications

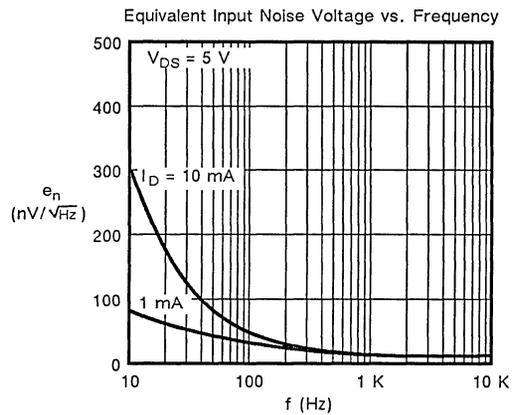
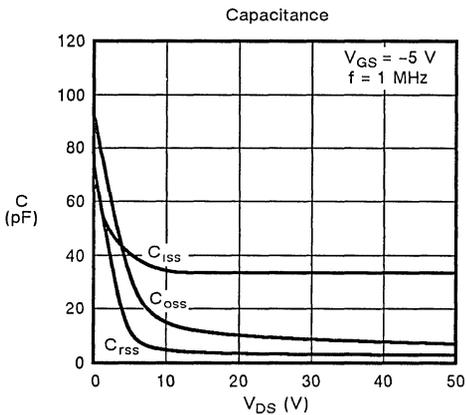
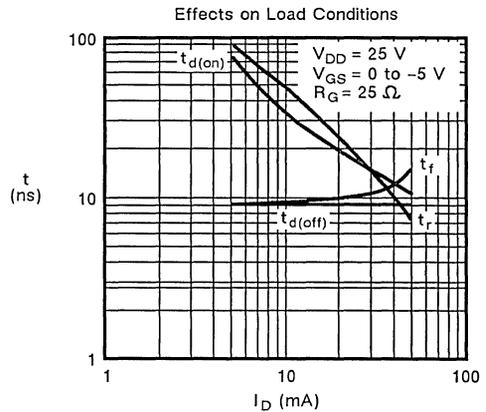
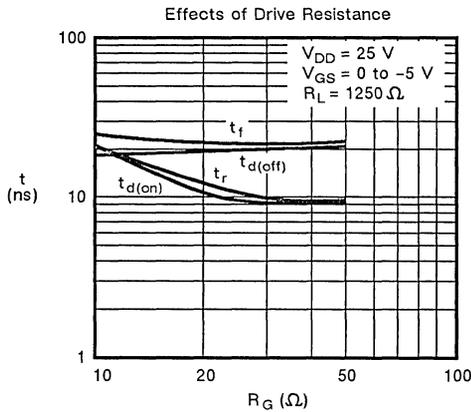
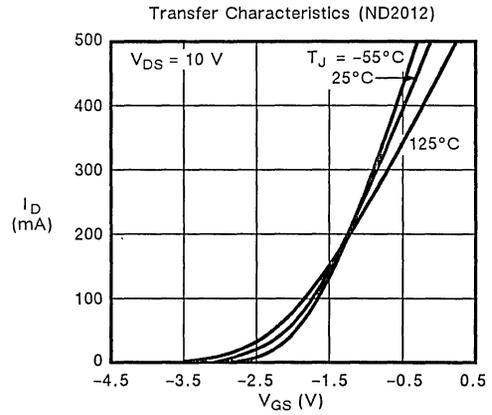
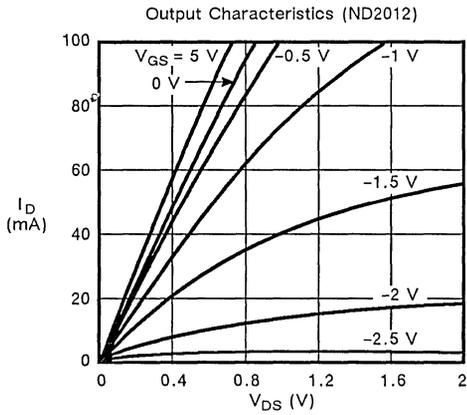
GEOMETRY DIAGRAM



TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS

